

**REMARKS**

By this Amendment, Claims 9 and 19 have been revised to correct the dependency thereof, and Claims 10, 20 and 29 have been revised to correct minor typographical errors.


Claims 1-34 remain pending in the application.

In response to the election of species requirement, Applicants elect Species II, to which at least claims 1-10 are directed. The election is without traverse.

Respectfully submitted,

KOJI TANIZAWA

By:

  
Adam C. Volentine  
Reg. No. 33,289

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JONES VOLENTINE, PLLC  
12200 Sunrise Valley Drive, Suite 150  
Reston, VA 20191  
(703) 715-0870

## ATTACHMENT "A"

### Additions/Deletions to Claims 9, 10, 19, 20 and 29:

9. (Amended) A nitride semiconductor device according to Claim [±] 8, wherein said n-region nitride semiconductor layer structure further includes an undoped GaN layer and an n-contact layer containing an n-type impurity, successively formed on said substrate.

10. (Amended) A nitride semiconductor device according to Claim 9, wherein said [~~n-type first~~] n-region multi-film layer is formed on said n-contact layer, and the total thickness of said undoped GaN layer, said n-contact layer, and said [~~n-type first~~] n-region multi-film layer falls within the range of 2 through 20 $\mu$ m.

19. (Amended) A nitride semiconductor device according to Claim [±±] 18, wherein said n-region nitride semiconductor layer structure further includes an undoped GaN layer and an n-contact layer containing an n-type impurity, successively formed on said substrate.

20. (Amended) A nitride semiconductor device according to Claim 19, wherein said [~~n-type first~~] r-region multi-film layer is formed on said n-contact layer, and the total thickness of said undoped GaN layer, said n-contact layer, and said [~~n-type first~~] n-region multi-film layer falls within the range of 2 through 20 $\mu$ m.

29. (Amended) A nitride semiconductor device according to Claim 26, wherein said p-type low-doped layer is made of  $\text{Al}_s\text{Ga}_{1-s}\text{N}$  ( $0 < s < 0.5$ ), and said p-type low - doped layer has a composition ratio of Al less than that of said first p-type [multi-film] layer.